2SD1618

Bipolar Transistor 15V, 0.7A, Low VCE(sat), NPN Single PCP



http://onsemi.com

Features

- · Low collector-to-emitter saturation voltage
- · Very small size making it easy to provide highdensity, small-sized hybrid IC's

Specifications

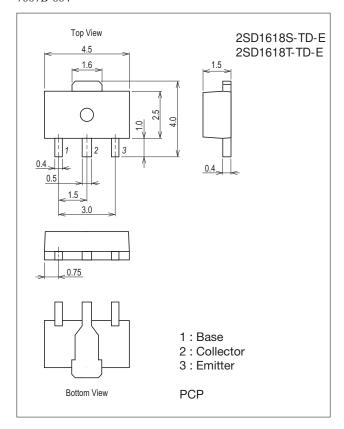
Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		20	V
Collector-to-Emitter Voltage	VCEO		15	V
Emitter-to-Base Voltage	VEBO		5	V
Collector Current	IC		0.7	Α
Collector Current (Pulse)	ICP		1.5	Α
Collector Dissipation	PC		500	mW
		When mounted on ceramic substrate (250mm ² ×0.8mm)	1.3	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Package Dimensions

unit : mm (typ) 7007B-004



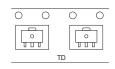
Product & Package Information

• Package : PCP

• JEITA, JEDEC : SC-62, SOT-89, TO-243

• Minimum Packing Quantity: 1,000 pcs./reel

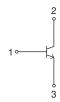
Packing Type: TD



Marking



Electrical Connection



2SD1618

Electrical Characteristics at Ta=25°C

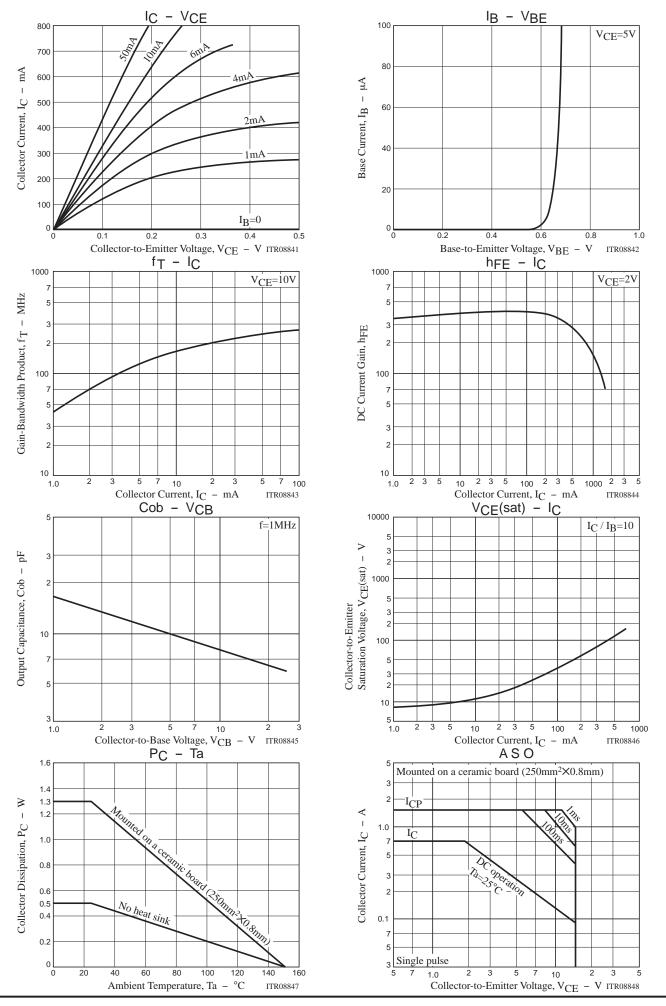
Parameter	Symbol	Conditions	Ratings			Unit	
raiametei Symbol		Conditions	min	typ	max	Oill	
Collector Cutoff Current	ICBO	V _{CB} =15V, I _E =0A			0.1	μΑ	
Emitter Cutoff Current	IEBO	V _{EB} =4V, I _C =0A			0.1	μΑ	
DC Current Gain	hFE1	V _{CE} =2V, I _C =50mA	140*		560*		
	hFE2	V _{CE} =2V, I _C =500mA	60				
Gain-Bandwidth Product	fŢ	V _{CE} =10V, I _C =50mA		250		MHz	
Collector-to-Emitter Saturation Voltage	V _{CE} (sat)1	I _C =5mA, I _B =0.5mA		10	25	mV	
	V _{CE} (sat)2	IC=100mA, IB=10mA		30	80	mV	
Base-to-Emitter Saturation Voltage	V _{BE} (sat)	I _C =100mA, I _B =10mA		0.8	1.2	V	
Collector-to-Base Breakdown Voltage	V(BR)CBO	IC=10μA, IE=0A	20			V	
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	IC=1mA, RBE=∞	15			V	
Emitter-to-Base Breakdown Voltage	V(BR)EBO	I _E =10μA, I _C =0A	5			V	
Output Capacitance	C _{ob}	V _{CB} =10V, f=1MHz		8		pF	

$\mbox{\ensuremath{^{\star}}}$: The 2SD1618 is classified by 50mA hFE as follows :

Rank	S	Т	U	
hFE	140 to 280	200 to 400	280 to 560	

Ordering Information

Device	Package	Shipping	memo	
2SD1618S-TD-E	PCP	1,000pcs./reel	Db Free	
2SD1618T-TD-E	PCP	1,000pcs./reel	Pb Free	

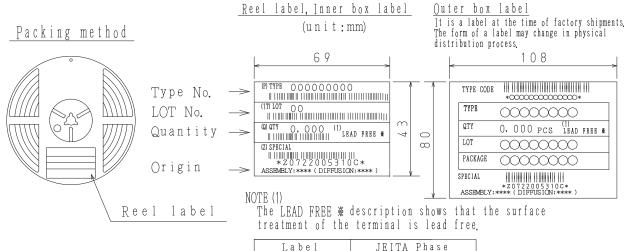


Bag Packing Specification

2SD1618S-TD-E, 2SD1618T-TD-E

1. Packing Format

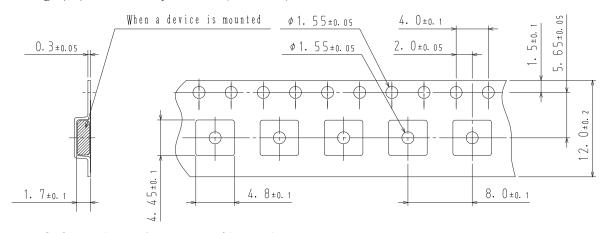
Package Name	Carrier Tape	Maximum Number of devices contained (pcs)			Packing	Packing format	
	Туре	Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)	
PCP	PCP	1, 000	4,000	24, 000	4 reels contained	6 inner boxes contained	
					Dimensions:mm (external)	Dimensions:mm (external)	
					183×72×185	440×195×210	



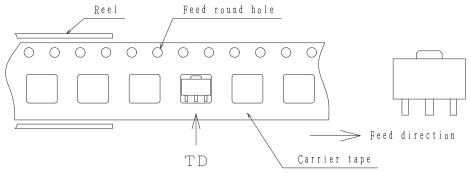
LEAD FREE 3 JEITA Phase 3A LEAD FREE 4 JEITA Phase 3

2. Taping configuration

2-1. Carrier tape size (unit:mm)



2-2. Device placement direction



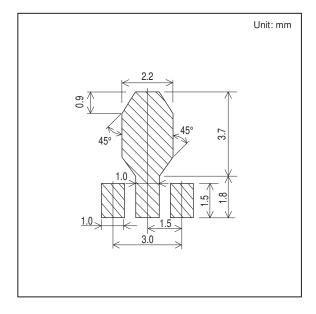
Those with pin 1 index on the feed hole side·····TD

Outline Drawing

2SD1618S-TD-E, 2SD1618T-TD-E

Mass (g) Unit 0.058 *For reference mm 4. 5±0. 1 1. 6±0. 2 _ 1.5±0.1_ 2. 5±0. 1 4. 0±0. 2 1. 0±0. 2 0. 4+0. 08 0. 4±0. 03 0. 5^{+0. 05} 1. 5±0. 2 3. O±0. 2 0. 75 0.10 *1:Lot indication

Land Pattern Example



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